**TOSHIBA** 

## TOSHIBA DIODE SILICON EPITAXIAL SCHOTTKY BARRIER TYPE

# 155319

#### LOW VOLTAGE HIGH SPEED SWITCHING.

Low Forward Voltage: VF(3)=0.54V (Typ.)

Low Reverse Current :  $I_R = 5\mu A$  (Max.)

Small Package : SC-61

## MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL RATING		UNIT	
Maximum (Peak) Reverse Voltage	$v_{RM}$	45	V	
Reverse Voltage	$V_{\mathbf{R}}$	40	V	
Maximum (Peak) Forward Current	$I_{FM}$	300 (*)	mA	
Average Forward Current	IO	100 (*)	mA	
Power Dissipation	P	150 (*)	mW	
Junction Temperature	$T_{ m j}$	125	$^{\circ}\mathrm{C}$	
Storage Temperature Range	$ m T_{stg}$	-55~125	$^{\circ}\mathrm{C}$	

Unit in mm 0.85 + 0.25 1.50 - 0.15  $0.05 \pm 0.05$ CATHODE 1 CATHODE 2 ANODE 2 ANODE 1 **JEDEC EIAJ** SC-61 **TOSHIBA** 2-3J1A

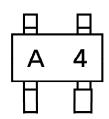
Weight: 0.013g

(\*) Unit Rating. Total Rating=Unit Rating×1.5.

## ELECTRICAL CHARACTERISTICS (Ta = 25°C)

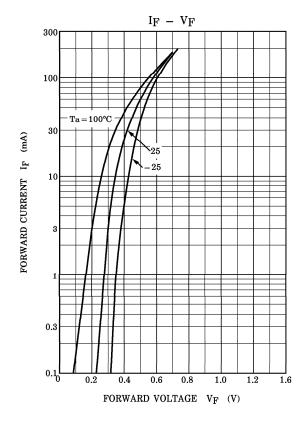
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	V <sub>F(1)</sub>	$I_{\mathbf{F}} = 1 \text{mA}$	-	0.28	_	
	$V_{F(2)}$	$I_{\mathbf{F}} = 10 \text{mA}$		0.36	_	V
	$V_{F(3)}$	$I_{ m F}$ = 100mA	I	0.54	0.60	
Reverse Current	${ m I}_{ m R}$	$V_R = 40V$	1	_	5	$\mu$ A
Total Capacitance	${ m C_T}$	$V_R=0$ , f=1MHz	_	18	25	рF

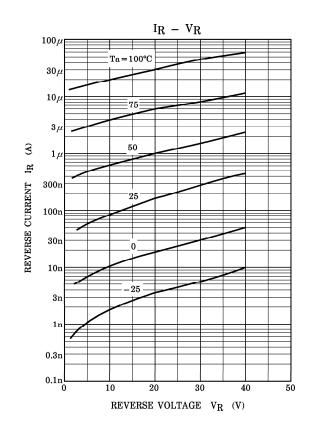
**MARKING** 

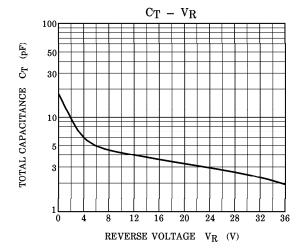


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